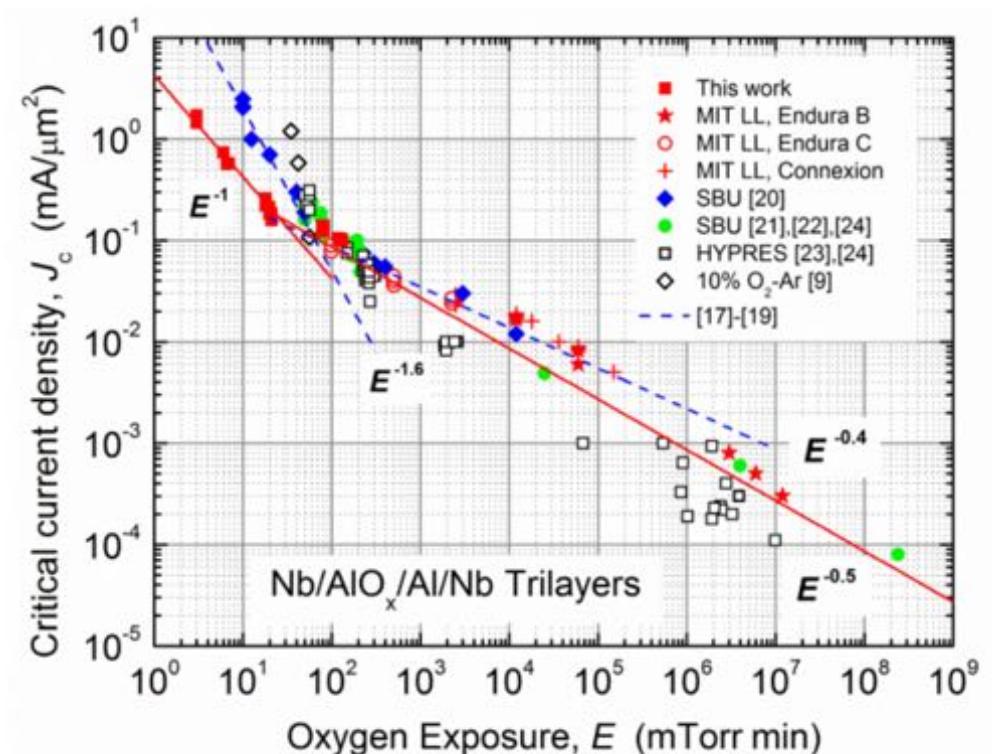


# Uniformity of Aluminum Oxide Barrier Conductivity as Obtained by Ambient Temperature C-AFM Mapping

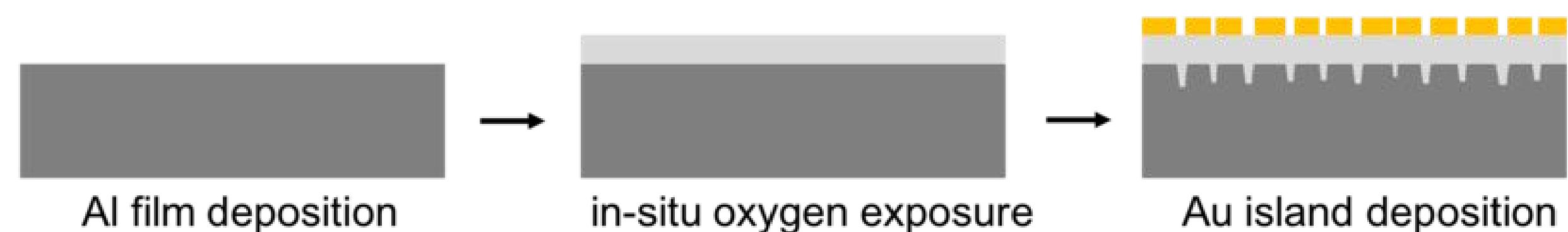
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## Motivation:

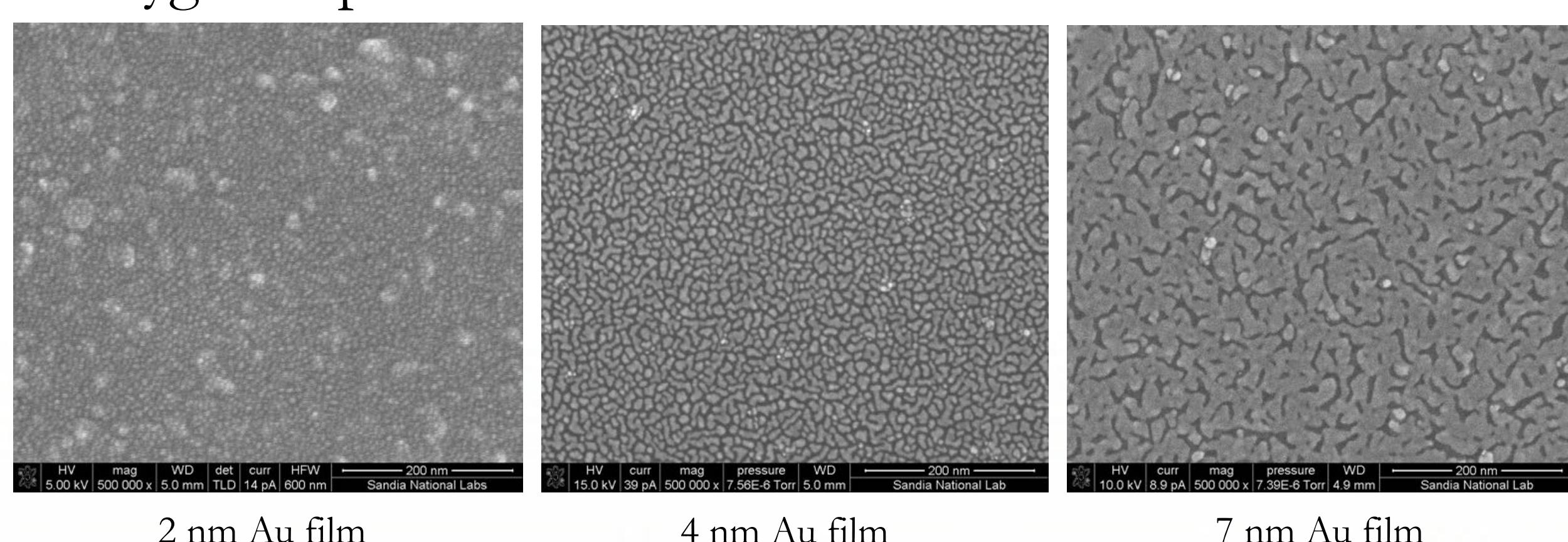
- Critical current density in  $\text{AlO}_x$  junctions decreases non-linearly with oxygen exposure
- What are the causes for critical current density drop?
- Can non-uniformities of the  $\text{AlO}_x$  barriers be imaged with conductive AFM?



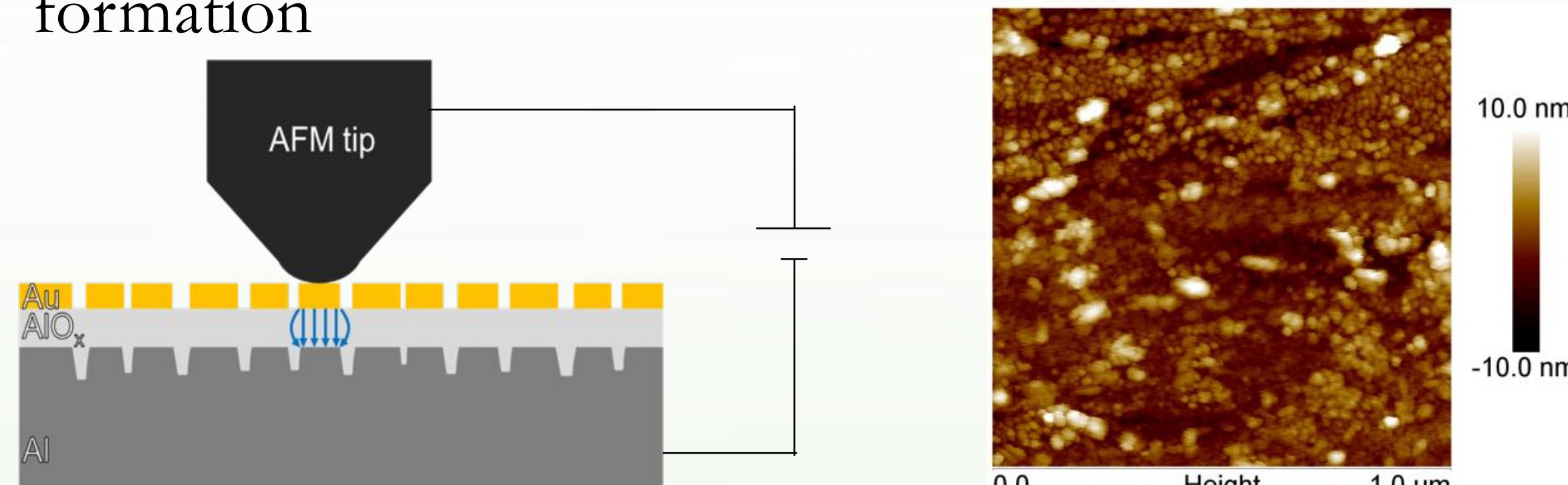
## Approach:



- Al films are evaporated onto Si substrates and exposed to oxygen in-situ in a dynamic flow
- Au islands are deposited subsequently, capping small areas and preventing further oxidation
- Oxygen exposure: 5 mTorr min and 10 mTorr min



- Au film of 4 nm leads to the most uniform island formation



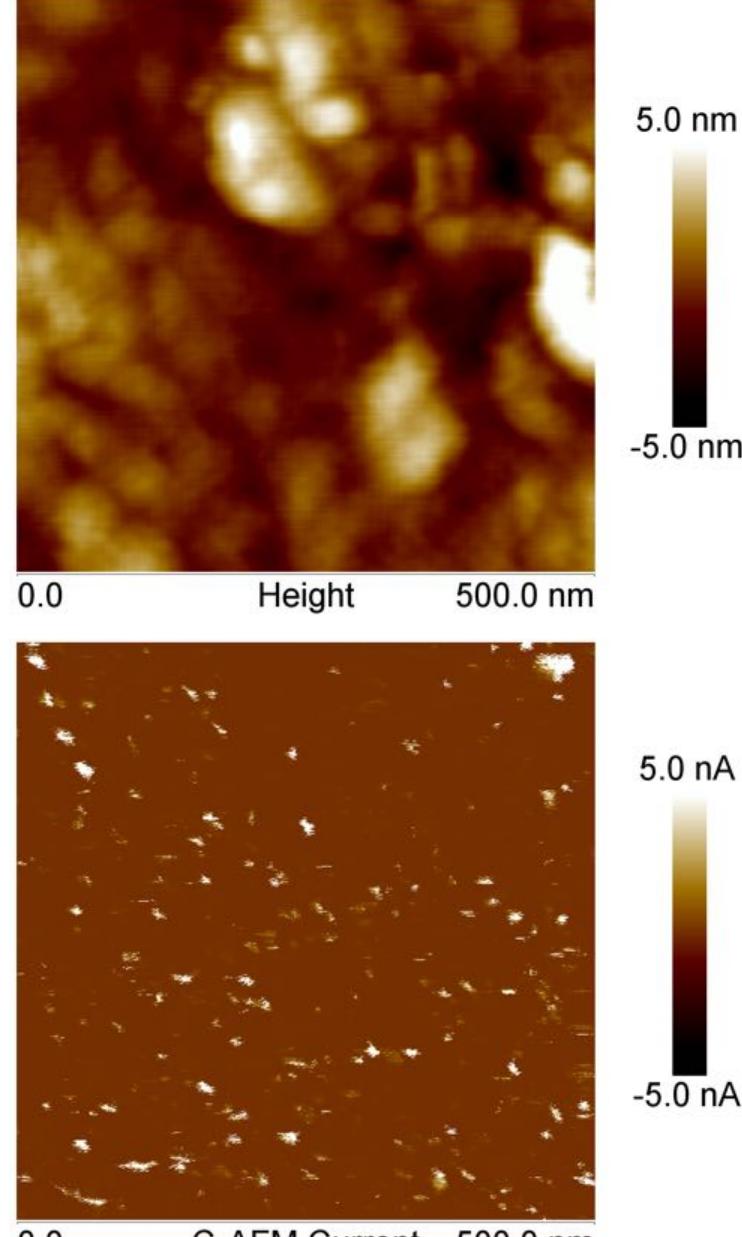
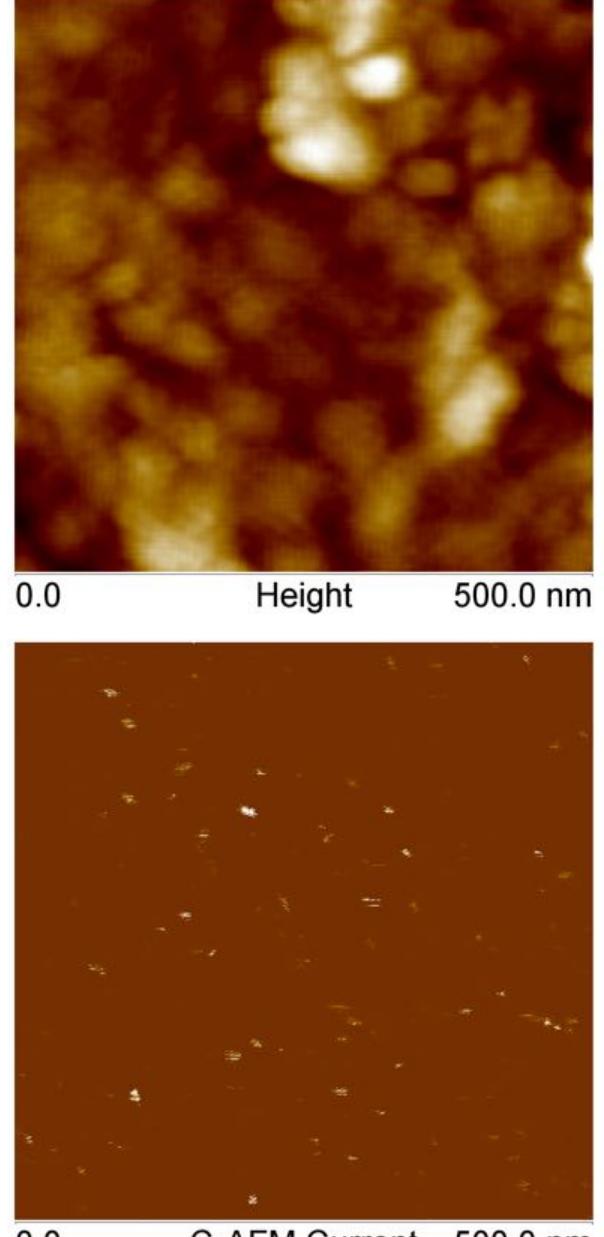
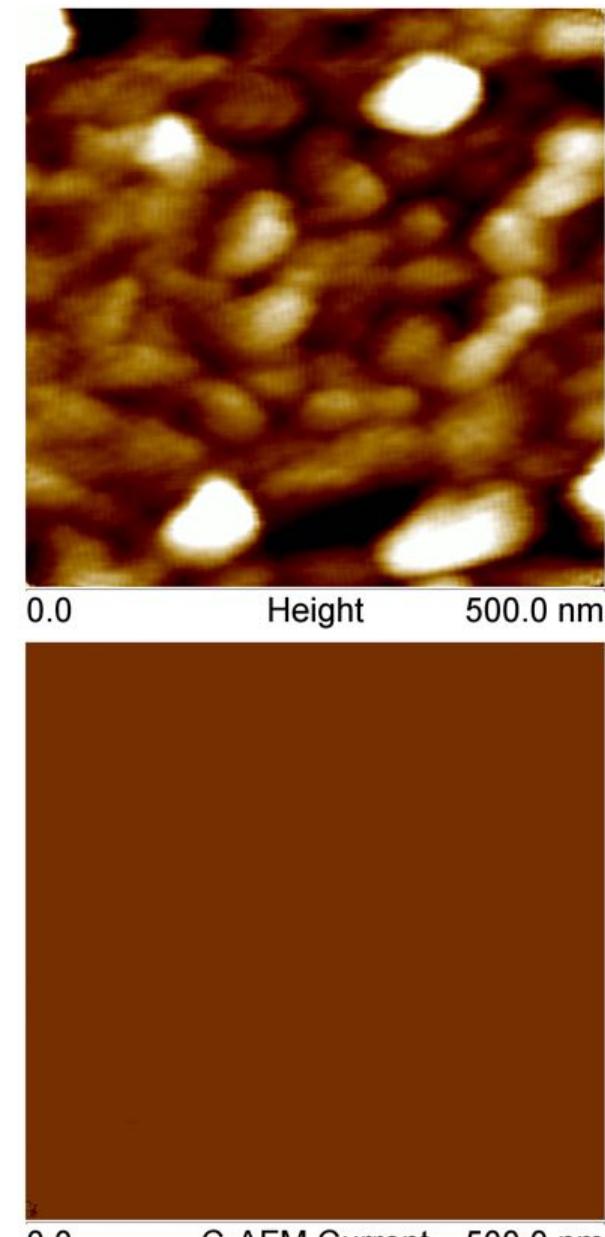
- Conductive AFM scanning across islands results in localized current measurement, exposing non-uniform current distribution

## Conductive Atomic Force Microscopy:

### Oxygen Exposure: 5 mTorr min

- Increasing applied bias results in the detection of localized areas of higher electronic conduction or “hot spots”
- “Hot spot” density increases with applied bias
- “Hot spots” do not appear to be correlated with underlying Al/AlOx morphology

#### Topography



0 mV

250 mV

1000 mV

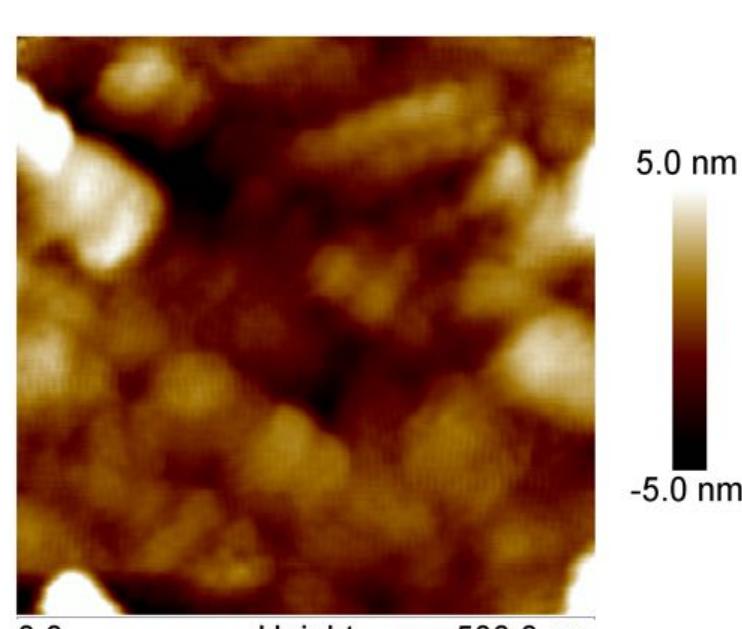
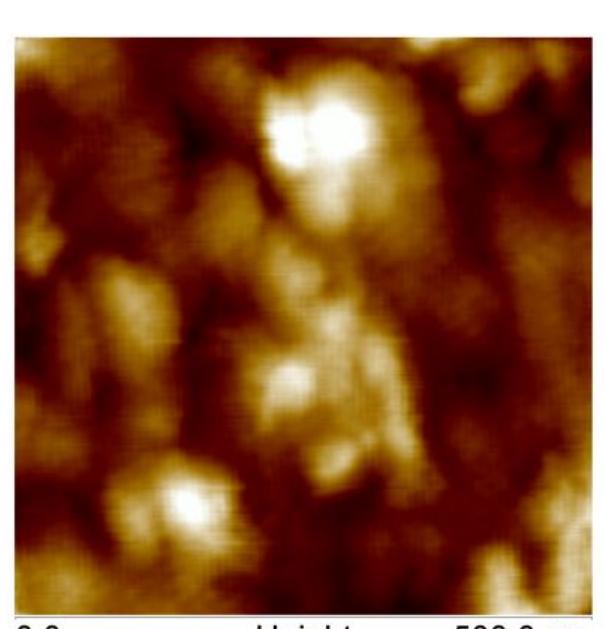
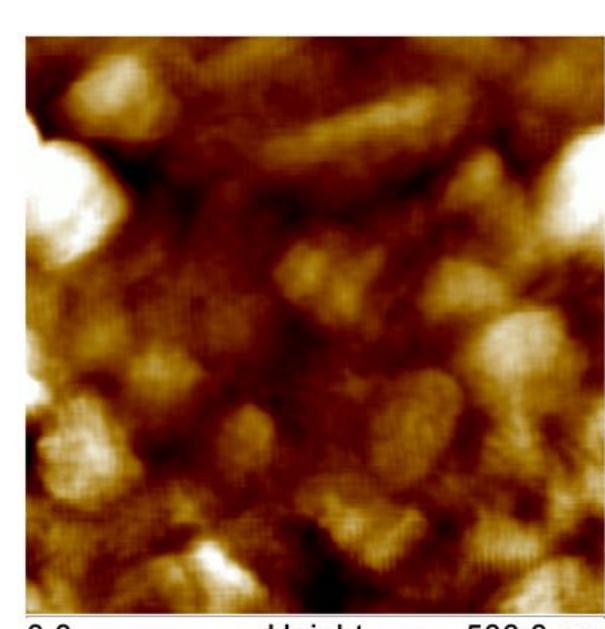
#### Current with increasing bias



### Oxygen Exposure: 10 mTorr min

- Increasing applied bias results in the detection of localized areas of higher electronic conduction or “hot spots”
- “Hot spot” density increases with applied bias
- “Hot spots” do not appear to be correlated with underlying Al/AlOx morphology

#### Topography

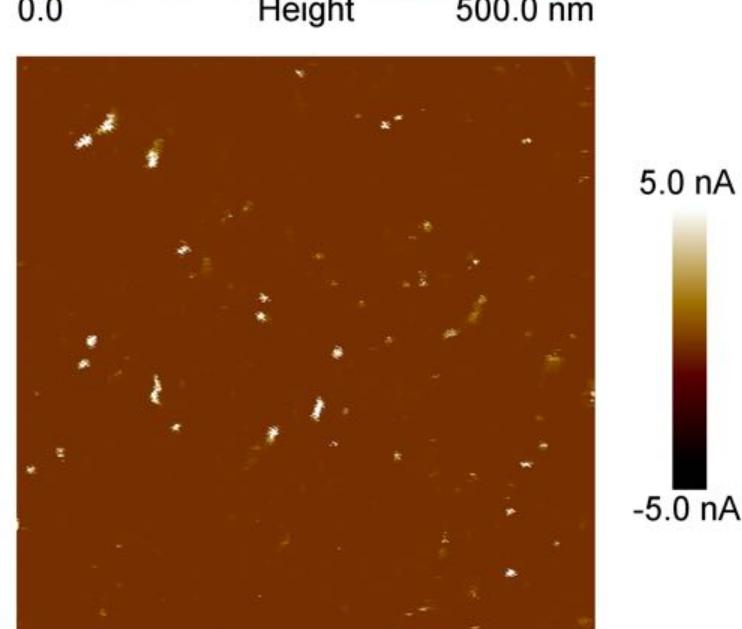
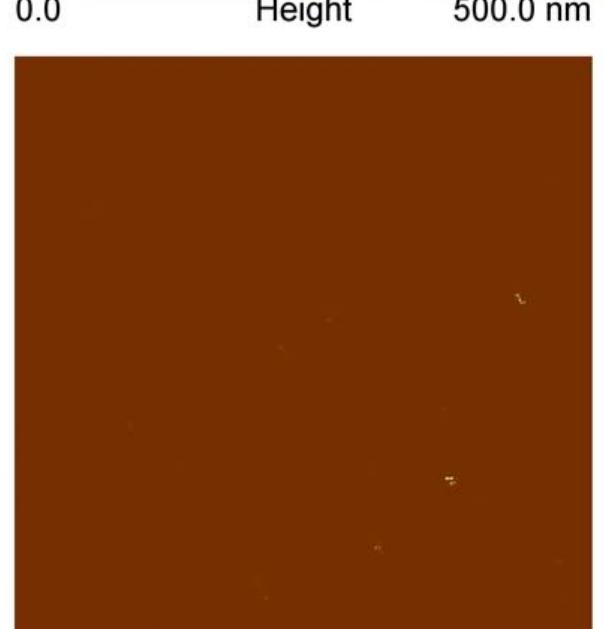


0 mV

250 mV

1000 mV

#### Current with increasing bias



## Summary:

- C-AFM allows for the study of non-uniform electronic conduction in  $\text{AlO}_x$  thin films
- Localized areas of electronic conduction are observed that do not appear to correlate with underlying Al/AlOx morphology
- Higher oxygen exposure, corresponding to thicker AlOx, requires higher bias to observe localized areas of electronic conduction